

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

ECH8601R — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance.
- · Built-in gate protection resistor.
- 2.5V drive.
- · Best suited for LiB charging and discharging Switch.
- · Common-drain type.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ΙD		6.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm) 1unit	1.4	W
Total Dissipation	PT	Mounted on a ceramic board (900mm ² X0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3.5A	7.0	10		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =4A, V _G S=4.5V		17	23	mΩ
	RDS(on)2	ID=4A, VGS=4.0V		18	24	mΩ
	R _{DS} (on)3	I _D =4A, V _G S=3.1V		20	30	mΩ
	R _{DS} (on)4	I _D =2A, V _G S=2.5V		24	35	mΩ
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		1140		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		420		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		190		pF

Marking: WB Continued on next page.

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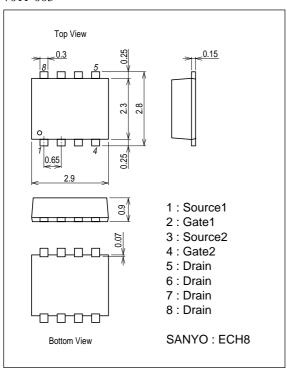
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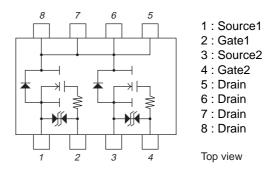
Parameter	Symbol	Conditions	Ratings			Unit
	Symbol		min	typ	max	Offic
Turn-ON Delay Time	td(on)	See specified Test Circuit.		425		ns
Rise Time	t _r	See specified Test Circuit.		1500		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		4000		ns
Fall Time	tf	See specified Test Circuit.		2860		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =6.5A		26.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =6.5A		1.4		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =6.5A		5.1		nC
Diode Forward Voltage	V _{SD}	I _S =6.5A, V _{GS} =0V		0.75	1.2	V

Package Dimensions

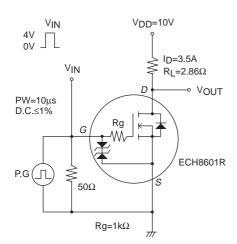
unit : mm 7011-003



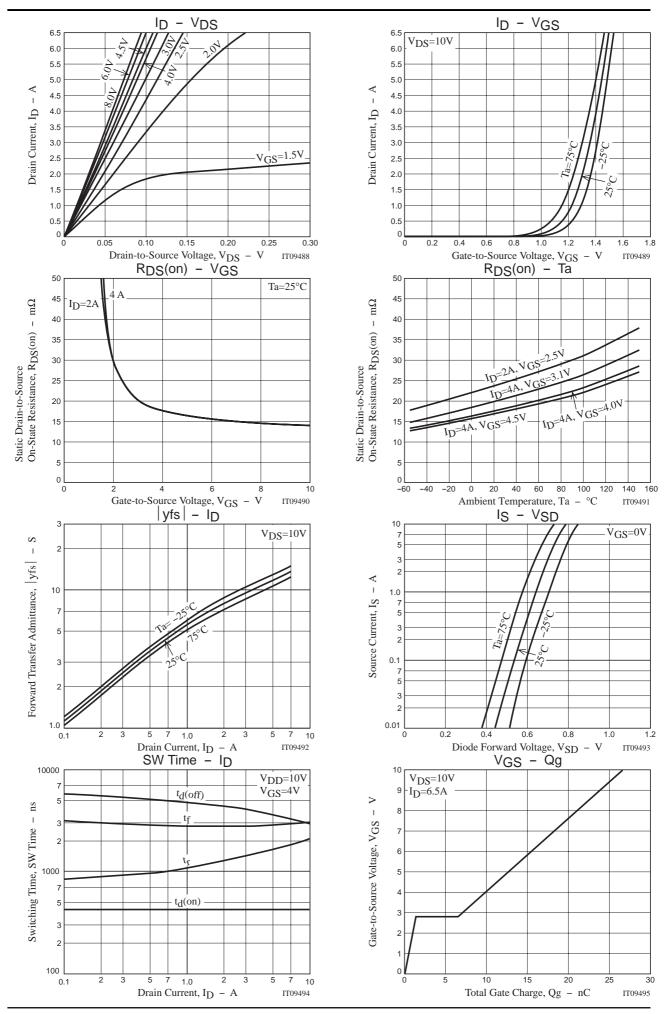
Electrical Connection



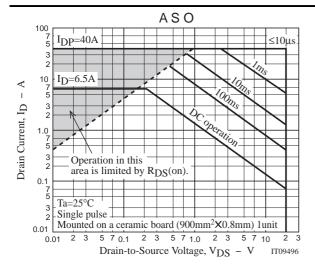
Switching Time Test Circuit

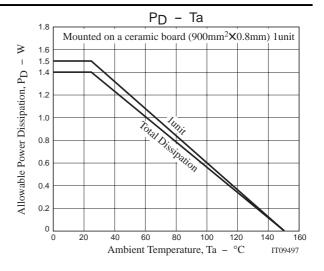


ECH8601R



ECH8601R





Note on usage: Since the ECH8601R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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